

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI TVV020** is Designed for Television Band III Applications up to 225 MHz.

FEATURES:

- Common Emitter
- $P_G = 8.0$ dB at 20 W/225 MHz
- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	8.0 A
V_{CEO}	35 V
V_{CES}	60 V
V_{EBO}	4.0 V
P_{DISS}	140 W @ $T_C = 25^\circ C$
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	1.5 °C/W

PACKAGE STYLE .500 4L STUD

DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	1.010 / 25.65	1.050 / 26.67
B	.220 / 5.59	.230 / 5.84
C	.495 / 12.57	.505 / 12.83
D	.003 / 0.08	.007 / 0.18
E	.160 / 4.06	.180 / 4.57
F	.622 / 15.80	
G	.100 / 2.54	.130 / 3.31
H	.415 / 10.54	.425 / 10.80
I	.720 / 18.29	
J	.250 / 6.35	.290 / 7.37

ORDER CODE: ASI10659

CHARACTERISTICS $T_C = 25^\circ C$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CBO}	$I_C = 50$ mA	65			V
BV_{CER}	$I_C = 50$ mA $R_{BE} = 10 \Omega$	60			V
BV_{CEO}	$I_C = 50$ mA	35			V
BV_{EBO}	$I_E = 10$ mA	4.0			V
I_{CES}	$V_{CB} = 50$ V			5.0	mA
h_{FE}	$V_{CE} = 5.0$ V $I_C = 1.0$ A	20		120	---
C_{OB}	$V_{CB} = 30$ V $f = 1.0$ MHz			85	pF
P_G IMD_3	$V_{CE} = 25$ V $I_C = 2.5$ A $f = 225$ MHz $P_{OUT} = 20$ W	8.0 -51			dB dBc